

GaAs IC SPDT 10 W T/R Switch DC–2.5 GHz



AW002R2-11

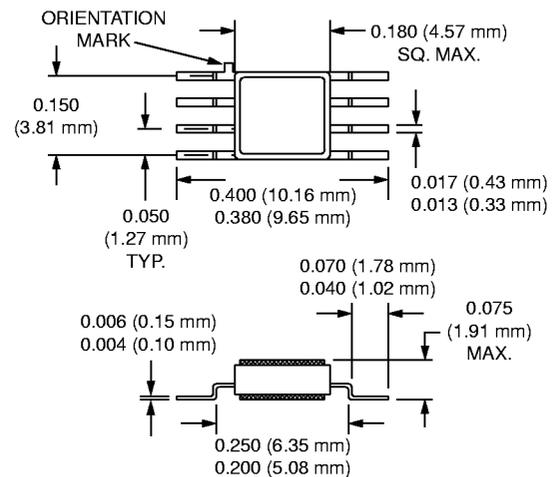
Features

- High Intercept Point (IP3 63 dBm @ 0.9 GHz)
- High Power, T/R Switch
- 8 Lead Hermetic Surface Mount Package
- Capable of Meeting MIL-STD Requirements⁶

Description

The AW002R2-11 is a high power IC FET SPDT switch. This switch has been designed for use where extremely high linearity is required. Some standard implementations include antenna changeover, T/R and diversity switching. This switch can be used in many analog and digital wireless communication systems.

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Electrical Specifications at 25°C (0, -5 V)

Parameter ¹	Frequency ⁵	Min.	Typ.	Max.	Unit
Insertion Loss ²	DC–0.5 GHz		0.7	0.8	dB
	DC–1.0 GHz		0.8	0.9	dB
	DC–2.5 GHz		1.0	1.1	dB
Isolation	DC–0.5 GHz	33	37		dB
	DC–1.0 GHz	28	30		dB
	DC–2.5 GHz	20	22		dB
VSWR ³	DC–1.0 GHz		1.2:1	1.4:1	dB
	DC–2.5 GHz		1.5:1	1.7:1	dB

Operating Characteristics at 25°C (0, -5 V)

Parameter	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching Characteristics	Rise, Fall (10/90% or 90/10% RF)			6		ns
	On, Off (50% CTL to 90/10% RF)			12		ns
	Video Feedthru ⁴			30		mV
Input Power for 1 dB Compression	5 V	0.9 GHz		35		dBm
	10 V	0.9 GHz		40		dBm
Intermodulation Intercept Point	For Two-tone Input Power 13 dBm					
	IP2	0.9 GHz		75		dBm
	IP3	0.9 GHz		63		dBm
Control Voltages	$V_{Low} = -12.0\text{ V} \leq V_{Low} \leq 0\text{ V}, 500\ \mu\text{A Max.}$ $V_{High} = 0\text{ V} \leq V_{High} \leq 12.0\text{ V}, 500\ \mu\text{A Max.}$ Differential = $5.0\text{ V} \leq (V_{High} - V_{Low}) < 12.0\text{ V}$					

1. All measurements made in a 50 Ω system, unless otherwise specified.

2. Insertion loss changes by 0.003 dB/°C.

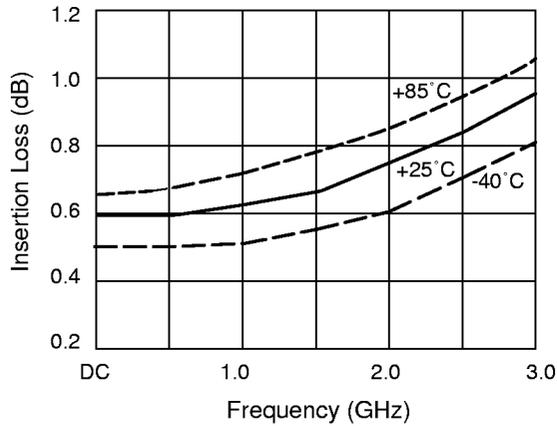
3. Insertion loss state.

4. Video feedthru measured with 1 ns risetime pulse and 500 MHz bandwidth.

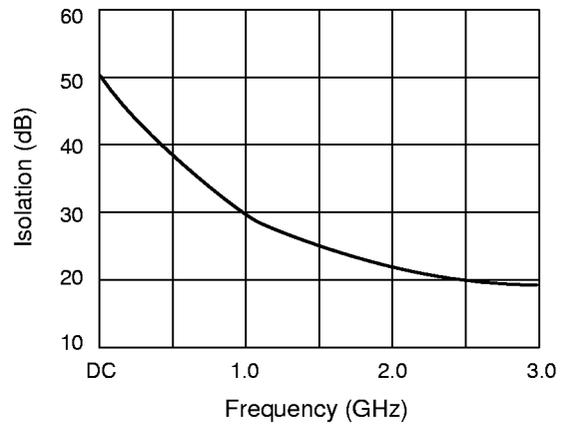
5. DC = 300 kHz.

6. See Quality/Reliability section.

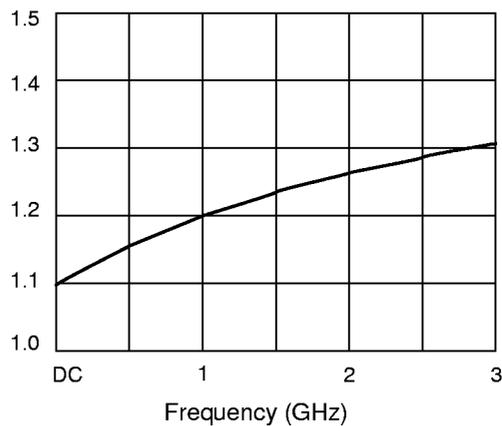
Typical Performance Data (0, -5 V)



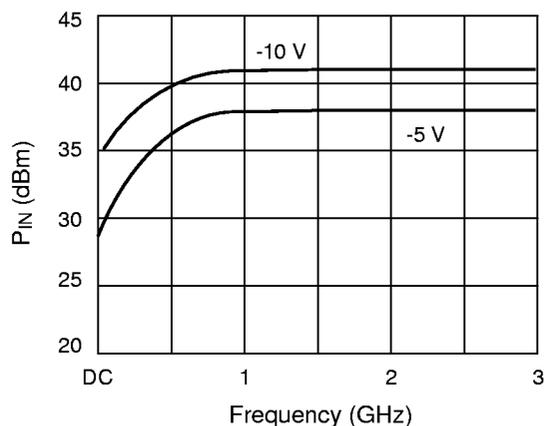
Insertion Loss vs. Frequency



Isolation vs. Frequency



VSWR vs. Frequency



P_{IN} at 1 dB Compression vs. Frequency and Control Voltage

Absolute Maximum Ratings

Characteristic	Value
RF Input Power (RF In)	11 W > 0.9 GHz, 0, -12 V
Control Voltage (V _C)	<12 V
Operating Temperature (T _{OP})	-40°C to +85°C
Storage Temperature (T _{ST})	-65°C to +150°C
Thermal Resistance (θ _{JC})	85°C/W

Truth Table

V ₁	V ₂	J ₁ -J ₂	J ₁ -J ₃
V _{Low}	V _{High}	Insertion Loss	Isolation
V _{High}	V _{Low}	Isolation	Insertion Loss

Pin Out

